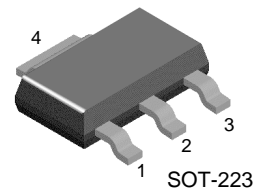


# NZT902

## NPN Low Saturation Transistor

- These devices are designed with high current gain and low saturation voltage with collector currents up to 3A continuous.



1. Base 2. Collector 3. Emitter

### Absolute Maximum Ratings\* $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	90	V
$V_{CBO}$	Collector-Base Voltage	120	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current - Continuous	3	A
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	- 55 ~ +150	$^\circ\text{C}$

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**NOTES:**

- 1) These ratings are based on a maximum junction temperature of  $150^\circ\text{C}$ .
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics\* $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$P_D$	Total Device Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	$^\circ\text{C/W}$

\* Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm.

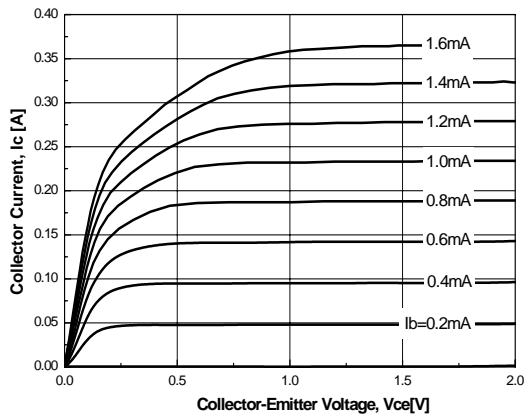
### Electrical Characteristics\* $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10\text{mA}$	90			V
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\mu\text{A}$	120			V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100\mu\text{A}$	5			V
$I_{CBO}$	Collector-Base Cutoff Current	$V_{CB} = 100\text{V}$ $V_{CB} = 100\text{V}, T_a = 100^\circ\text{C}$			100 10	nA uA
$I_{EBO}$	Emitter-Base Cutoff Current	$V_{EB} = 4\text{V}$			100	nA
$h_{FE}$	DC Current Gain	$I_C = 0.1\text{A}, V_{CE} = 2\text{V}$ $I_C = 1\text{A}, V_{CE} = 2\text{V}$ $I_C = 2\text{A}, V_{CE} = 2\text{V}$	80 80 25			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 0.1\text{A}, I_B = 5.0\text{mA}$ $I_C = 1\text{A}, I_B = 100\text{mA}$ $I_C = 3\text{A}, I_B = 300\text{mA}$			50 250 600	mV mV mV
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 1\text{A}, I_B = 100\text{mA}$			1.25	V
$C_{obo}$	Output Capacitance	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$			35	pF
$f_T$	Transition Frequency	$I_C = 100\text{mA}, V_{CE} = 5\text{V}, f = 100\text{MHz}$	75			MHz

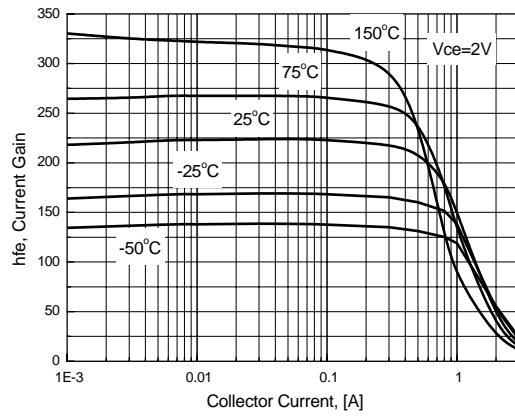
\* Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

## Typical Performance Characteristics

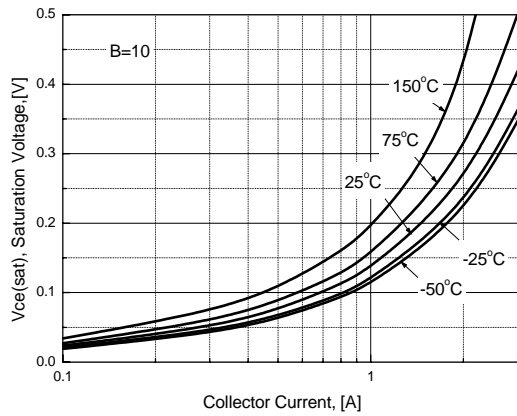
**Figure 1. Static Characteristic**



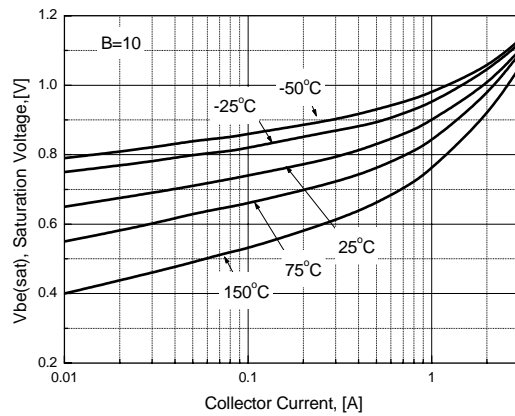
**Figure 2. DC current Gain**



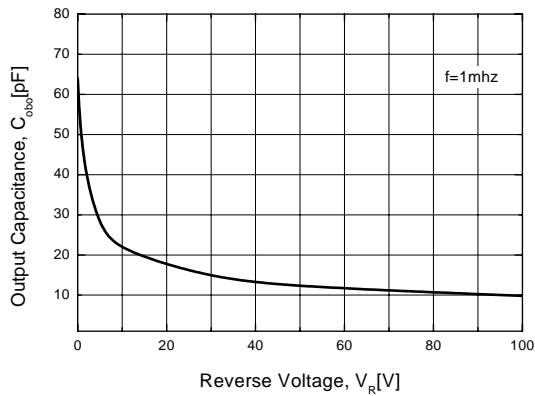
**Figure 3. Collector-Emitter Saturation Voltage**



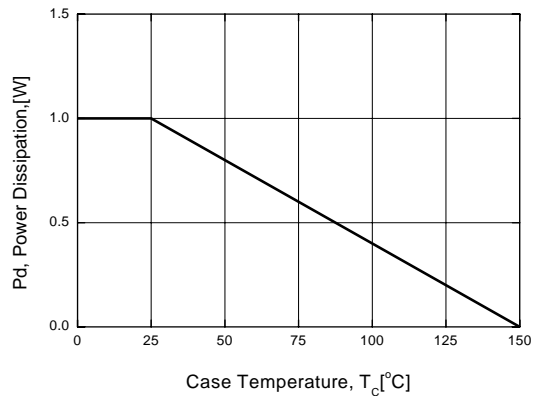
**Figure 4. Base-Emitter Saturation Voltage**



**Figure 5. Output Capacitance**

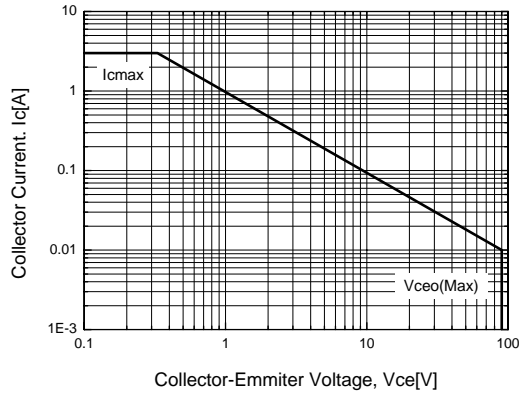


**Figure 6. Power Dissipation vs Ambient Temperature**



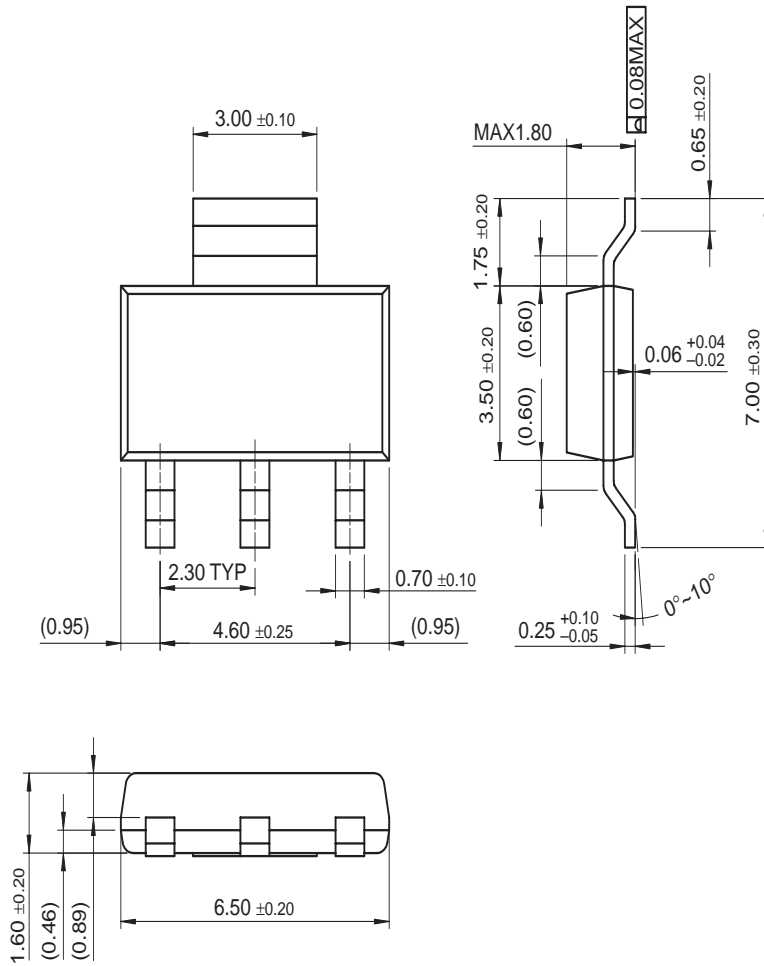
### Typical Performance Characteristics

Figure 9. SOA



# Mechanical Dimensions

## SOT-223



Dimensions in Millimeters

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CoolFET™	l <sup>2</sup> C™	PACMAN™	SuperFET™	
CROSSVOLT™	i-Lo™	POPT™	SuperSOT™-3	
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E <sup>2</sup> CMOS™	ISOPLANAR™	PowerSaver™	SyncFET™	
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FACT™	MICROCOUPLER™	QFET®	TinyBoost™	
FAST®	MicroFET™	QS™	TinyBuck™	
FASTr™	MicroPak™	QT Optoelectronics™	TinyPWM™	
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Rev. I20